OPA9430W1D

Infrared LED Chip

GaAlAs/GaAs

1. Material

Substrate	GaAs	(N Type)
Epitaxial Layer	GaAlAs	(P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

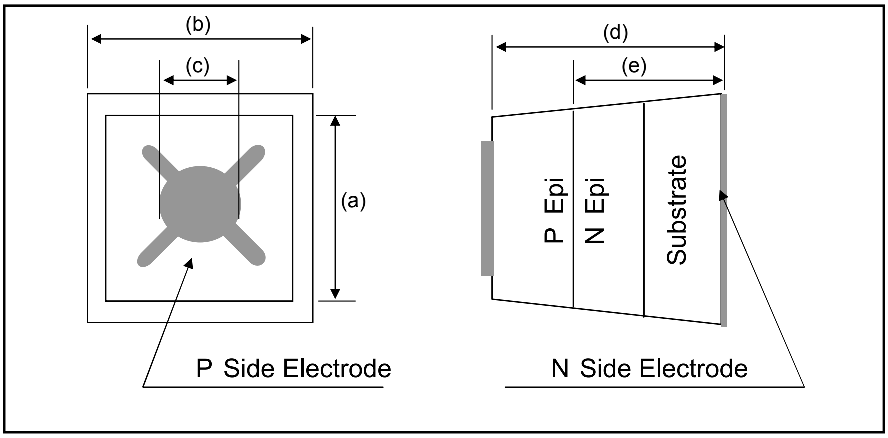
3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.55	1.60	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	17	22		mW	IF=100mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area ---------------------------- 11.0mil x 11.0mil
(b) Bottom Area ---------------------------- 12.0mil x 12.0mil
(a) Emission Area ---------------------------- 120um
(a) Emission Area ---------------------------- 8mil
(e) Junction Height ---------------------------- 4mil



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